

ABSTRACT

An object of the present invention is to provide a flip-chip-type gallium nitride compound semiconductor light-emitting device exhibiting excellent ohmic characteristics, excellent bonding characteristics, and high emission output.

The inventive flip-chip-type gallium nitride compound semiconductor light-emitting device comprises a positive electrode which has a three-layer structure comprising an ohmic electrode layer composed of rhodium which is in contact with the p-type semiconductor layer, an adhesion layer composed of titanium which is provided on the ohmic electrode layer and has a thickness of 10 Å or more, and a bonding pad layer provided on the adhesion layer and being composed of a metal selected from the group consisting of gold, aluminum, nickel, and copper, or composed of an alloy containing at least one of these metals.